

PATENT ABSTRACTS OF JAPAN

(11)Publication num r : 07-070752
(43)Date of publication of application : 14.03.1995

(51)Int.CI.	C23C 16/40 H01B 1/08 H01B 12/06 H01B 13/00
(21)Application number :	05-217266
(22)Date of filing :	01.09.1993
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(54) FILM FORMING METHOD OF OXIDE SUPERCONDUCTOR

(57)Abstract:

PURPOSE: To improve the smoothness of a film and improve crystallizability in the atomic layer epitaxy film forming.

CONSTITUTION: In the film forming method of the oxide superconductor forming the atomic layer epitaxy film of the oxide superconductor consisting of the compnd. containing more than three component metal element, the process in which plural metal elements consisting of one part of an unit latice is laminated simultaneously as one unit is included. In the film forming method of $RBa_2 Cu_3O_{7-\delta}$ (R is either one among Y, La, Pr, Nd, Sm, Eu, Gd, Dy, Ho, Er and Yb), the simultaneously laminating process of Cu, R and Cu as a subunit in order of Ba/Cu, R and Cu/Ba/Cu is included.

LEGAL STATUS

- [Date of request for examination]
- [Date of sending the examiner's decision of rejection]
- [Kind of final disposal of application other than the examiner's decision of rejection or application converted registration].
- [Date of final disposal for application]
- [Patent number]
- [Date of registration]
- [Number of appeal against examiner's decision of rejection]
- [Date of requesting appeal against examiner's decision of rejection]
- [Date of extinction of right]